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Substitute for form 1449B/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  Date Submitted: April 12, 2004  (use as many sheets as necessary)		<b>Complete if Known</b>	
		Application Number	Unassigned 10/821 921
Sheet 1 of 1		Filing Date	04/12/2004
		First Named Inventor	Yuichi OSHIMA
		Group Art Unit	2811
		Examiner Name	Unassigned
		Attorney Docket Number	035532-0141

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code <sup>2</sup> (if known)			
DS	A1	2002/0197825	A1	USUI ET AL.	12-26-2002	
DS	A2	6,555,845	B2	SUNAKAWA ET AL.	04-29-2003	

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		Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)				
<i>DS</i>	A3	JP	2003-178984	A	NEC CORP., ET AL.	06-27-2003		Abst.
<i>DS</i>	A4	JP	10-312971	A	NEC CORP.	11-24-1998		Abst.
<i>DS</i>	A5	JP	63-188983	A	RICOH CO., LTD., ET AL.	08-04-1988		Abst.

NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>6</sup>	
DS	A6	Ok-Hyun Nam et al., "Lateral Epitaxy of Low Defect Density GaN Layers via Organometallic Vapor Phase Epitaxy", Appl. Phys. Lett. 71 (18), 3 November 1997, pages 2638-2640.		
DS	A7	M. Kuramoto et al., "Room-Temperature Continuous-Wave Operation of InGaN Multi-Quantum-Well Laser Diodes Grown on an n-GaN Substrate with a Backside n-Contact", Jpn. J. Appl. Phys., Vol. 38, (1999), pages L184 -L186.		
DS	A8	T. Zheleva et al., "Pendeo-Epitaxy – A New Approach for Lateral Growth of Gallium Nitride Structures", MRS Internet J. Nitride Semicond. Res. 4S1, G3.38 (1999), 3 pages.		

Examiner Signature		Date Considered	6/12/06
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